



U.S. DEPARTMENT OF COMMERCE

PATENT AND TRADEMARK OFFICE

SECOND SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT BY APPLICANT

ATTY. DOCKET NO.	APPLN. NO.
ELM/001 Cont. 10	10/700,429
APPLICANTS	CONF. NO.
Glenn J. Leedy	5639
FILING DATE	GROUP ART UNIT
November 9, 2003	3729

U.S. PATENT DOCUMENTS

EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
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EN	DE 32 33 195	03/17/83	Germany				
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OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

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Complete if known Substitute for form 1449/PTO 10/700,429 **Application Number** Filing Date November 3, 2003 INFORMATION DISCLOSURE First Named Inventor Glenn J. Leedy STATEMENT BY APPLICANT Art Unit 3729 **Examiner Name** Carl J. Arbes (use as many sheets as necessary) of **Attorney Docket Number** ELM-1 CONT.10 Sheet

	U.S. PATENT DOCUMENTS								
Examiner Cite	Cite	Document Number	Publication Date	Name of Patentee or	Pages, Columns, Lines, Where Relevant Passages or Relevant				
initials*	No.1	Number – Kind Code ² (if known)	MM-DD-YYYY	Applicant of Cited Documents	Figures Appear				
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				Application Number	10/700,429 (Conf. No.: 5639)	
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Examiner Initials	Cite No.1	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-Issue number(s), publisher, city and/or country where published	7*						
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All References Have Been Considered: Examiner

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Substitute for form 1449/PTO INFORMATION DISCLOSURE				Complete if known		
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STATEMENT BY APPLICANT			PLICANT	First Named Inventor	Glenn J. Leedy	
,				Art Unit	3729	
(use as many sheets as necessary)			necessary)	Examiner Name	Carl J. Arbes	
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Sn		WO 1992 017901	10-15-1992	Integrated System Assemblies Corporation		
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Sub	Stitute for form 1449/VO/PT	•	•	Application Number	10/700,429	(Conf. No. 5639)	
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	4,251,909	02/24/81	Hoeberechts	29	580	
	4,262,631	04/21/81	Kubacki	118	723MP	
	4,394,401	07/19/83	Shioya et al.	427	574	
	4,401,986	08/30/83	Trenkler et al.	340	870.32	
	4,416,054	11/22/83	Thomas et al.	29	572	
	4,539,068	09/03/85	Takagi et al.	156	614	·
	4,585,991	04/29/86	Reid et al.	324	158 P	
	4,612,083	09/16/86	Yasumoto et al.	156	633	
	4,617,160	10/14/86	Belanger et al.	264	40.1	
	4,618,397	10/21/86	Shimizu et al.	156	628	
	4,618,763	10/21/86	Schmitz	250	211R	
	4,663,559	05/05/87	Christensen	313	336	
	4,684,436	08/04/87	Burns et al.	216	65	
47	4,693,770	09/15/87	Hatada	156	151 .	

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FORM PTO-1449 U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE				ATTY, DOCKET NO. ELM-1 Cont. 10		APPLICATION NO. 10/700,429		
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	STATEMENT			Glenn J. Le		5639		
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a.				<u></u>	Τ			
	4,702,336	10/27/87	Maeda et al.	180	197			
· \	4,702,936	10/27/87	Seibert et al.	427	583			
	4,706,166	11/10/87	Go	361	403			
	4,721,938	01/26/88	Stevenson	338	4			
	4,761,681	08/02/88	Reid	357	68			
	4,784,721	11/15/88	Holmen et al.	156	647			
	4,810,673	03/07/89	Freeman	438	386	•		
	4,825,277	04/25/89	Mattox et al.	257	639			
	4,857,481	08/15/89	Tam et al.	438	619			
	4,924,589	05/15/90	Leedy	438	6			
	4,940,916	07/10/90	Borel et al.	313	306			
	Re B14,940,916	11/26/96	Borel et al.	315	306			
	4,950,987	08/21/90	Vranish et al.	324	207.23			
	4,952,446	08/18/90	Lee et al.	428	220			
	4,954,865	09/04/90	Rokos	257	378			
ť	4,957,882	09/18/90	Shinomiya	438	65			
	4,965,415	10/23/90	Young et al.	200	83 N			
	4,966,663	10/30/90	Mauger	205	656			
	4,994,735	02/19/91	Leedy	324	158			
	5,008,619	04/16/91	Keogh et al.	324	207.17			
	5,010,024	04/23/91	Allen et al.	438	659			
	5,020,219	06/04/91	Leedy	29	846			
	5,034,685	07/23/91	Leedy	324	158 F			
	5,070,026	12/03/91	Greenwald et al.	437	3			
	5,071,510	12/10/91	Findler et al.	156	647			
	5,098,865	03/24/92	Machado et al.	438	788			
	5,103,557	04/14/92	Leedy	29	832			
 	5,110,373	05/05/92	Mauger	148	33.2			
	5,111,278	05/05/92	Eichelberger	357	75			
	5,116,777	05/26/92	Chan et al.	- 438	234			
	5,130,894	07/14/92	Miller	361	393			
-	5,132,244	07/21/92	Roy	438	477			

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FORM PTO-1449 U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE				ATTY. DOC ELM-1 Con		APPLICATION NO. 10/700,429		
	INFORMATION STATEMEN			APPLICAN [*] Glenn J. Le		CONFIRMATION NO. 5639		
		MAIN :	FILING DAT November 3		GROUP 3729			
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A	5,151,775	09/29/92	Hadwin [*]	357	80			
	5,156,909	10/20/92	Henager, Jr. et al.	428	334			
	5,203,731	04/20/93	Zimmerman	445	24			
	5,225,771	07/06/93	Leedy	324	158	V.		
	5,236,118	08/17/93	Bower et al.	228	193			
	5,262,351	11/16/93	Bureau et al.	437	183			
•	5,270,261	12/14/93	Bertin et al.	437	209			
	5,273,940	12/28/93	Sanders	437	209			
	5,274,270	12/28/93	Tuckerman	257	758			
	5,279,865	01/18/94	Chebi et al.	427	574			
	5,284,796	02/08/94	Nakanishi et al.	437	183			
	5,323,035	06/21/94	Leedy	257	48			
	5,324,687	06/28/94	Wojnarowski	437	225			
	5,354,695	10/11/94	Leedy	438	411			
	5,363,021	11/08/94	MacDonald	315	366			
	5,385,632	01/31/95	Goossen	156	630			
	5,385,909	01/31/95	Nelson et al.	514	291			
	5,420,458	05/30/95	Shimoji	257	622			
T	5,424,920	06/13/95	Miyake	361	735			
	5,426,072	06/20/95	Finnila	437	208			
	5,426,363	06/20/95	Akagi et al.	324	239			
	5,432,444	07/11/95	Yasohama et al.	324	240			
	5,432,729	07/11/95	Carson et al.	365	63			
	5,434,500	07/18/95	Hauck et al.	324	67			
	5,451,489	09/19/95	Leedy	430	313	·		
	5,453,404	09/26/95	Leedy	437	203			
	5,457,879	10/17/95	Gurtler et al.	29	895			
	5,476,813	12/19/95	Naruse ·	437	132			
	5,489,554	02/06/96	Gates	437	208			
	5,502,667	03/26/96	Bertin et al.	365	51			
h	5,512,397	04/30/96	Leedy	430	30			
47	5,527,645	06/18/96	Pati et al.	430	5			

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	5,529,829	06/25/96	Koskenmaki et al.	428	167			
	5,534,465	07/09/96	Frye et al.	437	209	`		
	5,555,212	09/10/96	Toshiaki et al.	365	200			
	5,563,084	10/08/96	Ramm et al.	437	51			
	5,571,741	11/05/96	Leedy	437	51			
	5,580,687	12/03/96	Leedy	430	5			
	5,581,498	12/03/96	Ludwig et al.	. 365	63			
	5,582,939	12/10/96	Pierrat	430	5			
	5,583,688	12/10/96	Hornbeck	359	291			
	5,592,007	01/07/97	Leedy	257	347			
	5,592,018	01/07/97	Leedy	257	619			
	5,595,933	01/21/97	Heijboer	439	20	=		
	5,606,186	02/25/97	Noda	257.	226			
	5,627,112	05/06/97	Tennant et al.	438	113			
	5,629,137	05/13/97	Leedy	430	313			
	5,633,209	05/27/97	Leedy	435	228			
	5,637,536	06/10/97	Val	438	686			
	5,654,127	08/05/97	Leedy	430	315			
	5,654,220	08/05/97	Leedy	438	25	·		
	5,656,552	08/12/97	Hudak et al.	438	15 ~			
	5,675,185	10/07/97	Chen et al.	257	774			
	5,694,588	12/02/97	Ohara et al.	395	566			
	5,725,995	03/10/98	Leedy	430	315			
	5,750,211	05/12/98	Weise et al.	427	579	•		
	5,760,478	06/02/98	Bozso et al.	257	777			
	5,773,152	06/30/98	Okonogi	428	446			
	5,786,116	07/28/98	Rolfson	430	5			
	5,793,115	08/11/98	Zavracky et al.	257	777			
 	5,831,280	11/03/98	Ray	257	48			
1	5,834,334	11/10/98	Leedy	438	107			
	5,840,593	11/24/98	Leedy	438	6	·		
Son	5,856,695	01/05/99	Ito et al.	257	370			

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FORM PTO-1449 U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE INFORMATION DISCLOSURE STATEMENT BY APPLICANT							ELM-1 Cont. 10 10 APPLICANT C			APPLICATION NO. 10/700,429 CONFIRMATION NO. 5639		
	·		_	:								
6/	£ 969 040	02/09/9	00	Sotokaw	o et el	٦	216	18	<u> </u>			
	5,868,949 5,869,354	02/09/9	_	Leedy	a et ai.	ᆉ	438	110				
	5,870,176	02/09/9		Sweatt e	t al	+	355	53				
	5,880,010	03/09/9		Davidsor		┪	438	455	- 			
	5,882,532	03/16/9	\neg	Field et a		\dashv	216	2				
		05/11/9		Hübner	11	+	438	106				
	5,902,118 5,915,167	06/22/		Leedy			438	108				
	5,946,559	08/31/9		Leedy		-	438	157				
	5,985,693	11/16/		Leedy		_	438	107				
	5,998,069	12/07/		Cutter et			430	5				
	6,008,126	12/28/9		Leedy	di.	-	438	667				
 						\dashv	438	626				
	6,020,257 6,045,625		02/01/00 Leedy 04/04/00 Houston			_	148	33.3				
	6,084,284	07/04/		Adamic,		1	257	506				
	6,097,096	08/01/		Gardner	-··		257	777				
	6,133,640	10/17/		Leedy	et al.	\dashv	257	778				
	6,194,245 B1	02/27/		Tayanak		\dashv	438	57	1.			
	6,197,456 B1	03/06/		Aleshin e		-	430	5	1	····		
	6,208,545 B1	03/27/		Leedy	, cai.	-	365	51				
	6,236,602 B1	05/22/		Patti			365	201	-			
	6,261,728 B1	07/17/	_	Lin	· · · · · · · · · · · · · · · · · · ·		430	30				
	6.288.561 B1	09/11/		Leedy		\dashv	324	760				
6	6,294,909 B1	09/25/	_	Leedy		\dashv	324	207.17				
	1 0,254,505 51	1 OUILUI			ATENT DOCUM	MEI		1.501.11				
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	GB 2,215,168		1	/1989	UK	1	09G	1/00				
	EP 0 189 976		-	/1986	EPO	1	101L	31/18				
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	STATEMENT BY	APPLICANT	FILING DATE November 3, 2003	-	GROUP 3729			
	JP 02-082564	03/1990	Japan			ABST		
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	JP 04-107964	04/1992	Japan			ABST		
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U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE

PLEMENTAL INFORMATION DISCLOSURE STATEMENT BY APPLICANT

ATTY. DOCKET NO.	APPLN. NO.
ELM/001 Cont. 10	10/700,429
APPLICANTS	CONF. NO.
Glenn J. Leedy	5639
FILING DATE November 3, 2003	GROUP ART UNIT 3729

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7	4,500,905	02/19/1985	Shibata	357	68	
	4,939,568	07/03/1990	Kato, et al.	357	75	
	4,892,753	01/09/1990	Wang, et al.	427	579	
	5,000,113	03/19/1991	Wang, et al.	118	723	
	5,240,458	08/31/1993	Linglain, et al.	464	63	
	5,259,247	11/09/1993	Bantien	73	718	
	RE 34,893	04/04/1995	Fujii, et al.	257	419	
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tr-	6,087,284	07/11/2000	Brix, et al.	501	69	
	6,518,073	02/11/2003	Momohara	438	4	12/10/2001

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INITIAL	NUMBER					YES	NO
a	04-196,263	07/1992	Japan				

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	ENTAL INFORMATION DISCLOSURE	APPLICANTS Glenn J. Leedy	CONF. NO. 5639
STATEMENT BY APPLICANT		FILING DATE November 3, 2003	GROUP ART UNIT 3729

EXAMINER INITIAL

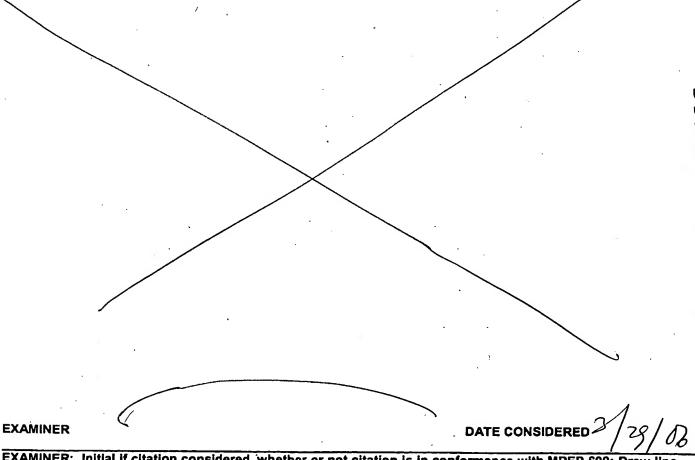
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EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not conformance and not considered. Include copy of this form with next communication to applicant.